

deposition (step 140) of a metal 50". It follows that the gate can be "entirely" covered on the top and sidewalls (as many as are exposed) by the conductive metal. This is now more clearly set forth in the claims.

Objection raised in the paragraph bridging pages 2 and 3 of the Office action has been overcome by amendment.

Claims 8 and 9 were rejected under 35 U.S.C. 112, second paragraph, as being indefinite. The rejection is respectfully traversed. The gate is recited in line 3 of each of these claims and therefore provides antecedent basis for the gate in the subsequent lines of these claims.

Claims 8 to 27 were rejected under 35 U.S.C. 103(a) as being unpatentable over Arai (U.S. 5,841,174) in view of Watabe et al.(4,727,038) and Tada (Japan 4-42938). It is noted that no translation of Tada has been provided and, accordingly, this is not a proper reference of record at present. The rejection is respectfully traversed.

Claims 8 and 9 require, among other features, a lateral growth on said gate dielectric at the corners of said gate, but not under central regions of the gate increasing the thickness of the gate dielectric at the interface of the bottom surface and the sidewalls. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references taken alone or in the combination as claimed. The advantages derived by the claimed structure are increased gate conductivity, additional control over gate corner profiles, additional control over gate electric fields, additional control over silicided gate structures and additional control over the line-to-space ratio of the gate pattern, while using conventional processes.

Claim 10 requires, among other features, a silicide layer disposed on said top and sidewalls of the polysilicon gate and source/drain regions in the region of semiconductor material spaced apart from each other and each disposed adjacent to and aligned with the silicide

layer disposed on the sidewalls. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references taken alone or in the combination as claimed.

Claims 12, 14, 16, 18, 20, 22, 24, 26 and 27 depend from claim 10 and therefore define patentably over the applied references for at least the reasons presented above with reference to claim 10.

Claim 12 further limits claim 10 by requiring that the silicide layer be titanium silicide. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references in the combination as claimed.

Claims 14 and 16 further limit claims 10 and 12 by requiring a lightly doped source/drain extension of each of the source/drain regions extending under the polysilicon gate. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references in the combination as claimed.

Claims 18, 20, 22 and 24 further limit claims 10, 12, 14 and 16 by requiring a dielectric extending from the gate dielectric of increased thickness relative to the gate dielectric and disposed under the silicide layer. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references either alone or in the combination as claimed.

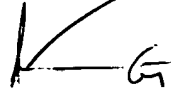
Claim 26 further limits claim 10 by requiring that the silicide layer extend to the gate dielectric. No such arrangement is taught or suggested by Arai, Watabe et al., Tada or any proper combination of these references either alone or in the combination as claimed.

Claim 27 further limits claim 18 by requiring that the silicide layer extend to said dielectric of increased thickness. No such arrangement is taught or suggested by Arai, Watabe et

al., Tada or any proper combination of these references either alone or in the combination as claimed.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,

A handwritten signature in black ink, appearing to be 'J. Cantor', with a long, sweeping horizontal line extending to the right.

Jay M. Cantor
Reg. No. 19906
(202) 639-7713